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INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)		Docket No.: 901.0120.U1(US) Applicant(s): Fletcher et al.. Filing Date: herewith		Serial No.: To be assigned Group: N/A	
U.S. PATENT DOCUMENTS					
Examiner Initials	Document Number (Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name of Patentee or Applicant	Class	Sub-class
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OTHER DOCUMENTS (Author (Capitalize), Title, Date, Pages, Etc., if known)					
LP	F. FOULON, L.ROUSSEAU, L.BABADJIAN, S.SPIRKOVITCH, A.BRAMBILLA and P.BERGONZO, "A New Technique for the Fabrication of Thin Silicon Radiation Detectors", pgs. 218-220, IEEE Transactions on Nuclear Science, Vol. 46, No. 3, June 1999,				
Examiner's Signature: <i>Long Pham</i>			Date Considered: <i>7/14/05</i>		
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).					